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## +3.6V, 1W Autoramping Power Amplifier for 900MHz Applications

## General Description

The MAX2235 low-voltage, silicon RF power amplifier (PA) is designed for use in the 900MHz frequency band. It operates directly from a single +2.7V to +5.5V supply, making it suitable for use with 3-cell NiCd or 1-cell Li-lon batteries. The device delivers +30dBm (1W) typical output power from a +3.6V supply or +28dBm from a +2.7V supply.

The MAX2235's gain is adjustable over a 37dB range. A power-control pin controls gain and bias to maintain optimum efficiency, even at lower output power levels, thus extending the operating life of the battery. At +30dBm output power, efficiency is typically 47%. An additional power-saving feature is a shutdown mode that typically reduces supply current below 1µA.

A key feature of this PA is its autoramping capability. During turn-on and turn-off periods, the RF envelope is controlled to approximate a raised cosine on the rising and falling edge, thereby minimizing transient noise and spectral splatter. The ramp time is set by selecting the value of an external capacitor.

The MAX2235 is intended for use in constant envelope applications such as AMPS, two-way paging, or FSKbased communications in the 900MHz ISM band. The device is available in a thermally enhanced 20-pin TSSOP package with a heat slug.

## Applications

900MHz ISM-Band Applications

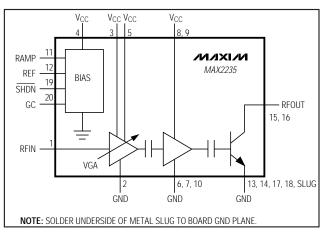
Two-Way Pagers

Analog Cellular Phones

Microcellular GSM (Power Class 5)

Wireless Data Networks

## Functional Diagram



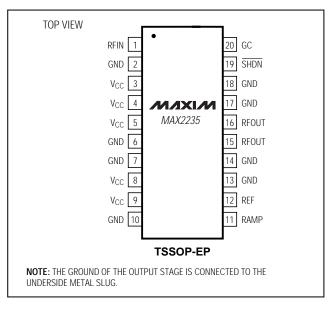
Features

- ♦ 800MHz to 1000MHz Operation
- ♦ High Output Power at 836MHz
  - +32.5dBm at +5.0V
  - +30dBm at +3.6V
  - +29dBm at +3.0V
  - +28dBm at +2.7V
- ♦ +2.7V to +5.5V Single-Supply Operation
- ♦ Automatic Power-Up/Power-Down Ramp
- ♦ Direct On/Off Keying (OOK) without Intersymbol Interference or VCO Pulling
- **♦ 37dB Power-Control Range**
- ♦ 47% Efficiency
- ♦ <1µA Supply Current in Shutdown Mode
  </p>
- **♦ Small 20-Pin TSSOP Package with Heat Slug**

## Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
MAX2235EUP	-40°C to +85°C	20 TSSOP-EP

## Pin Configuration



NIXIN

Maxim Integrated Products 1

### **ABSOLUTE MAXIMUM RATINGS**

VCC to GND0.3V to +6.5V
SHDN to GND0.3V to (V <sub>CC</sub> + 0.3V)
GC to GND0.3V to (V <sub>CC</sub> + 0.3V)
RF Input Power+13dBm (20mW)
Maximum Load Mismatch without Damage,
$V_{CC} = +2.7V$ to $+3.4V$ , Any Load Phase Angle,
Any Duration20:1
Maximum Load Mismatch without Damage,
$V_{CC} = +3.4V$ to +5.5V, Any Load Phase Angle,
Any Duration8:1

Continuous Power Dissipation ( $T_A = +70$ °C)	
TSSOP (derate $80 \text{mW/°C}$ above $T_A = +70 \text{°C}$ )	6.4W
Operating Temperature Range40	°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range65°C	
Lead Temperature (soldering, 10sec)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### DC ELECTRICAL CHARACTERISTICS

( $V_{CC}$  = +2.7V to +5.5V, GC = RAMP = REF = unconnected, no input signal applied,  $T_A$  = -40°C to +85°C, unless otherwise noted. Typical values are at  $V_{CC}$  = +3.6V and  $T_A$  = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
SHDN Logic High	ViH		2.0			V
SHDN Logic Low	VIL				0.5	V
Shutdown Supply Current		SHDN = GND		0.5	10	μА
	ISHDN	2.7V < V <sub>CC</sub> < 3.4V, SHDN = GND, T <sub>A</sub> = +55°C			1	
Standby Supply Current	ISTBY	V <sub>GC</sub> < 0.4			20	mA
CHON Input Current	livious	V SHDN = 2.0V			0.5	μΑ
SHDN Input Current	INSHDN	V <u>SHDN</u> < 0.5V	-0.5		0.5	
GC Input Current	IGC	V SHDN < 0.5V, VGC < 0.4V	-0.5		0.5	- μΑ
GC Input Current		V SHDN > 2.3V, VGC > 0.6V	-10		1.0	
GC Open-Circuit Voltage	VGCNOM		2.0	2.2	2.4	V

### **AC ELECTRICAL CHARACTERISTICS**

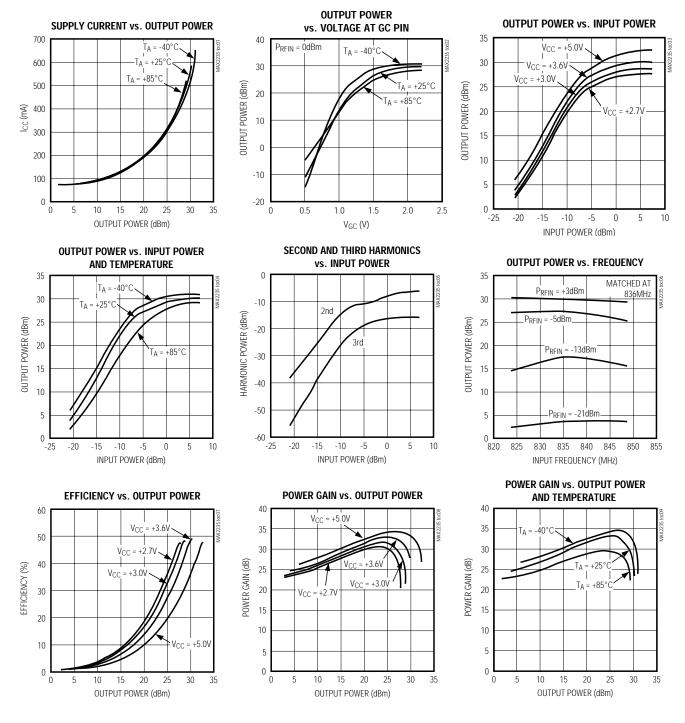
(MAX2235 Evaluation Kit, GC = unconnected, PRFIN adjusted to give PRFOUT = +30dBm, fRFIN = 836MHz, VCC =  $\overline{VSHDN}$  = +3.6V, TA = +25°C, unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL	COND	MIN	TYP	MAX	UNITS		
Operational Frequency Range (Note 2)	fRFIN			800		1000	MHz	
		Vcc = 5.0V			32.5			
	PRFOUT	Vcc = 3.6V			30.3		1	
Minimum Output Power		V <sub>CC</sub> = 3.0V (Note 2)	27.0	28.7		dBm		
		V <sub>CC</sub> = 3.0V, T <sub>A</sub> = T <sub>MIN</sub>	25.5			1		
		V <sub>CC</sub> = 2.7V			28.0		=	
Power Added Efficiency	PAE				47		%	
		PRFOUT = +30dBm			610			
Average Supply Current	Icc	P <sub>RFIN</sub> adjusted to give	$P_{RFOUT} = +24dBm$		315		mA	
Average supply current	100	P <sub>RFIN</sub> = 0dBm, V <sub>GC</sub> adjusted to give P <sub>RFOUT</sub> = 24dBm			305		IIIA	
Power Gain	GP			24	26		dB	
Gain-Control Range (Note 3)		0.6V < V <sub>GC</sub> < 2.3V			37		dB	
Auto-Power Ramping-Up Maximum Slope (Note 4)	dP/dt				1.6		mW/µs	
Auto-Power Ramping-Down Minimum Slope (Note 4)	dP/dt				-1.3		mW/µs	
Input VSWR	VSWR	50Ω source impedance			1.5:1			
Standby Mode Input VSWR Change	ΔVSWR	Input VSWR relative to input impedance in operating mode			1.5:1			
Maximum Nonharmonic Spurious Output Due to Load Mismatch		V <sub>CC</sub> = 2.7V to 5.5V, 6:1 VSWR at any phase angle			-60		dBc	
Noise Power		30kHz BW at offset = 45MHz			-90		dBm	
Harmonic Suppression (Note 5)		$P_{RFIN} = +7dBm$		30	38		dBc	
Off-Isolation		P <sub>RFIN</sub> = 0dBm	$V \overline{SHDN} = 0.5V$ 40		48		- dB	
OII-130IdtIOI1		GC = GND		25	36		GD	

- Note 1: Guaranteed by design and characterization.
- **Note 2:** For optimum performance at a given frequency, design the output matching network for maximum output power.
- Note 3: Gain is monotonic with V<sub>GC</sub>.
- Note 4: 0.068µF capacitor from RAMP to REF. Time is measured from \$\overline{SHDN}\$ low-to-high transition to +29dBm output power, or from \$\overline{SHDN}\$ high-to-low transition to -25dBm output power.
- **Note 5:** Harmonics measured on the evaluation kit, which provides some harmonic attenuation in addition to the rejection provided by the IC. The combined suppression is specified.

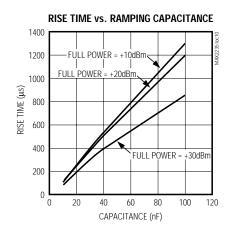
## Typical Operating Characteristics

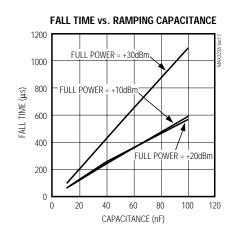
(MAX2235 Evaluation Kit, GC = unconnected,  $f_{RFIN} = 836MHz$ ,  $V_{CC} = V_{\overline{SHDN}} = +3.6V$ ,  $T_{A} = +25^{\circ}C$ , unless otherwise noted.)



## Typical Operating Characteristics (continued)

(MAX2235 Evaluation Kit, GC = unconnected,  $f_{RFIN} = 836MHz$ ,  $V_{CC} = V_{\overline{SHDN}} = +3.6V$ ,  $T_A = +25$ °C, unless otherwise noted.)

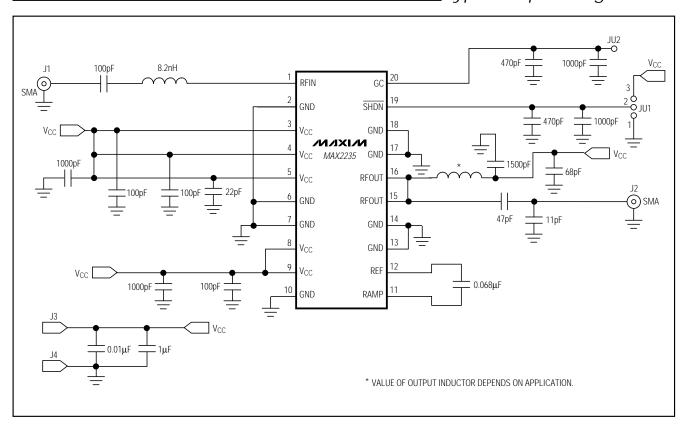




## Pin Description

PIN	NAME	FUNCTION			
1	RFIN	RF Input. A DC blocking capacitor in series with RFIN is required. The value of the capacitor depends the operating frequency.			
2	GND	GND connection for the input stage (variable-gain amplifier). Connect to the circuit board ground plane with a <i>separate</i> low-inductance path (via).			
3	Vcc	Supply Voltage Input for the Input Stage. Bypass with its own 100pF low-inductance capacitor to GND.			
4	Vcc	Supply Voltage Input for Bias Circuitry. Bypass with its own 100pF low-inductance capacitor and a 1000pF capacitor to GND, to minimize RF signal coupling into the bias circuits.			
5	Vcc	Supply Voltage Input for the Input Stage. Bypass with its own 22pF low-inductance capacitor to pins 6 and 7.			
6, 7, 10	GND Connection for the Second-Stage Amplifier (driver). Connect to the circuit board ground plane separate low-inductance path (via).				
8	Vcc	Supply Voltage Input for the Second Stage. Bypass with its own 220pF and 1000pF low-inductance capacitors to GND.			
9	Vcc	Supply Voltage Input for the Second Stage. Connect to pin 8.			
11	RAMP	Power Ramp Pin. Connect a capacitor between RAMP and REF to provide a gradual linear power-up/down ramp. See <i>Detailed Description</i> .			
12	REF	Reference Voltage for RAMP Capacitor. The reference is internally set to 1.9V.			
13, 14, 17, 18, SLUG	GND	GND Connection for the Power Stage. Solder the slug to the circuit board ground plane. Connect pins 13, 14, 17, and 18 to the slug with a straight board trace under the chip.			
15	Power Amplifier Output. See <i>Typical Operating Circuit</i> for an example of a matching networ vides optimal output power at 836MHz. Connect to pin 16.				
16	RFOUT	Power Amplifier Output. Connect to pin 15.			
19	SHDN	Shutdown Pin. Drive $\overline{\text{SHDN}}$ low to turn the device off. Drive above 2.0V to turn the device on. Drive V $\overline{\text{SHDN}}$ > 2.0V and V <sub>GC</sub> < 0.4V for standby mode.			
20	GC	Gain-Control Pin. Apply V <sub>GC</sub> between 0.6V and 2.3V to control the output power with a monotonic dB/V relationship. See the <i>Typical Operating Characteristics</i> for a typical relationship.			

## Typical Operating Circuit



## Detailed Description

The MAX2235 power amplifier (PA) operates over a wide frequency range of 800MHz to 1000MHz. The signal path consists of three stages: the input stage, the driver stage, and the power stage. There are matching circuits between the first and second stages, and between the second and third stages. The bias circuits process external commands to control the device's power-up/down and the gain of the PA.

#### Input Stage

The first stage is a variable-gain amplifier with 37dB gain-control range. The input transistor acts as a transconductor with constant bias current. Gain control is achieved by steering the signal current from the input transistor to the first output matching network (to drive the second stage) or to a separate supply pin. This

stage operates in class A and remains on in standby mode to ensure that the VSWR at the input does not vary more than 1.5:1 compared with normal operation. The input stage typically requires an external inductor to achieve an optimum input VSWR.

#### Second Stage (Driver)

The driver produces a signal large enough to drive the power stage into saturation. The driver stage operates in Class C and is off during standby.

Second- and Third-Stage Matching

The interstage matching networks provide optimal loading and power transfer. The circuits are on-chip to save board space. The bandwidths of the matching networks allow the PA to operate over a wide frequency range.

#### Third Stage (Power Stage)

This last stage delivers 30dBm to a  $50\Omega$  load. It operates in Class E to achieve a high power-added efficiency (PAE). Proper output matching is required for optimal output power. The output of the power stage requires a low-series-resistance pull-up inductor with a minimum current rating of 1.5A. See the *Typical Operating Circuit* for an example of an output matching circuit.

### Biasing and Power Control

 $\overline{\text{SHDN}},$  GC, RAMP, and REF are bias and power-control pins. Drive  $\overline{\text{SHDN}}$  below 0.5V to turn off the entire chip, and drive  $\overline{\text{SHDN}}$  above 2.0V to turn on the device. When  $\overline{\text{SHDN}}$  is high, a VGC from 0.6V to 2.3V continuously controls the gain in the first stage (VGA) and the output power.

Drive GC below 0.4V to put the device in standby mode with only the first stage on. If GC is unconnected and  $V \ \overline{SHDN} > 2.0V$ , the device is set to maximum gain. Table 1 summarizes these operating modes.

### Power Ramping Control

A capacitor connected between RAMP and REF controls the output power rise/fall time to reduce transient noise when SHDN turns the device on and off. Because the ramp is approximately a raised cosine, this device can be used in direct On/Off Keying (OOK) applications with minimum intersymbol interference. The value of the ramping capacitor is determined from the Rise/Fall Time vs. Ramping Capacitance curves in the *Typical Operating Characteristics*.

**Table 1. Operating Modes** 

SHDN	GC	MODE
>2.0V	>0.6V	On
>2.0V	<0.4V	Standby
<0.5V	Don't care	Shutdown

#### **Board Assembly Precaution**

Solder the underside metal slug evenly to the board ground plane for optimal performance. Fill all vias in the area under the slug. For maximum power gain and saturated output power, ensure that the entire slug makes contact with the board ground.

\_\_\_\_\_Chip Information

TRANSISTOR COUNT: 668

\_Package Information

